

## IN THE CLAIMS:

Please cancel claims 1-5, 7-11, and 32-37 without prejudice.

1-17. (Canceled)

18. (Previously Presented) A method for pre-cleaning apertures on a substrate, the method comprising:

- disposing the substrate on a substrate support member in a process chamber;
- exposing an at least partially exposed copper layer on the substrate to a pre-clean process while maintaining a substrate temperature of less than about 100 degrees Celsius; and
- depositing a bulk layer of copper on the at least partially exposed copper layer.

19-37. (Canceled)

38. (Previously Presented) The method of claim 18, wherein the bulk layer of copper is formed by chemical vapor deposition, physical vapor deposition, electroplating, or spraying.

39. (Previously Presented) The method of claim 18, wherein the exposing the substrate to a pre-clean process comprises forming a plasma from a gas mixture comprising a non-reactive gas.

40. (Previously Presented) The method of claim 18, wherein the exposing the substrate to a pre-clean process comprises forming a plasma from a gas mixture consisting of argon.

41. (Previously Presented) The method of claim 39, wherein the gas mixture further comprises a reactive gas.

42. (Previously Presented) The method of claim 18, further comprising electrostatically chucking the substrate to the substrate support member.